



REMARKS

in order to place the instant application in better form for consideration on appeal, the subject matter of Claim 20 has been incorporated into Claim 18. Since this amendment results in the cancellation of a claim and places the instant application in better form for consideration on appeal, entry thereof is deemed proper under 37 CFR 1.116(b). Favorable consideration is respectfully solicited.

Respectfully submitted,


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Encl: Marked-Up Amended Claim 18
Postal Card

136.0112

18. (~~New~~Amended) A method of manufacturing a single crystal diamond p-type semiconductor having a thermal conductivity of from about 26-31 W/cm°K and a boron content not exceeding 100 ppm comprising the steps of:

providing a carbonaceous material containing isotopically purified ^{12}C or ^{13}C ;

providing a flux containing a nitrogen getter;

adding boron into the carbonaceous material or/and the flux, or around the carbonaceous material and the flux; and

diffusing the carbonaceous material into the flux under a high temperature and pressure to form a boron-doped single crystal diamond p-type semiconductor on a seed crystal diamond.

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